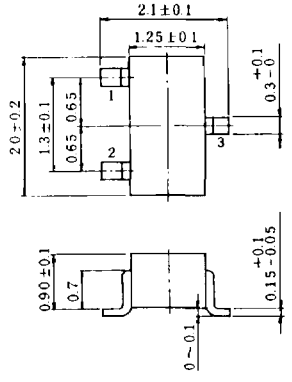
SILICON N CHANNEL JUNCTION TYPE
FIELD EFFECT TRANSISTOR

2SK881

FM TUNER APPLICATIONS.
VHF BAND AMPLIFIER APPLICATIONS.

- Low Noise Figure : NF = 2.5dB (Typ.) (f = 100MHz)
- High Forward Transfer Admittance
  : $|y_{fs}| = 9mS$ (Typ.)

Unit in mm



1. DRAIN
2. GATE
3. SOURCE

JEDEC	—
EIAJ	SC-70
TOSHIBA	2-2E1C

Weight : 0.006g

MAXIMUM RATINGS (Ta = 25°C)

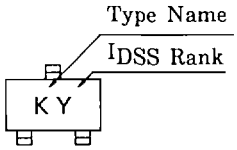
CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDO}	−18	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	100	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

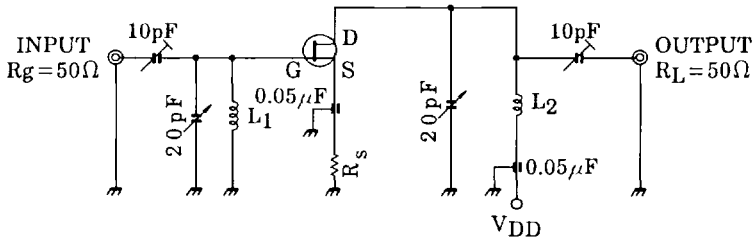
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS} = -0.5V$, $V_{DS} = 0$	—	—	−10	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDO}$	$I_G = -10\mu A$	−18	—	—	V
Drain Current	I_{DSS} (Note)	$V_{GS} = 0$, $V_{DS} = 10V$	1.0	—	10	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 10V$, $I_D = 1\mu A$	−0.4	—	−4.0	V
Forward Transfer Admittance	$\|y_{fs}\|$	$V_{GS} = 0$, $V_{DS} = 10V$, f = 1kHz	—	9	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 10V$, $V_{GS} = 0$, f = 1MHz	—	6.0	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V$, $V_{GS} = 0$, f = 1MHz	—	–	0.15	pF
Power Gain	G_{ps}	$V_{DD} = 10V$, f = 100MHz (Fig.1)	10	18	—	dB
Noise Figure	NF	$V_{DD} = 10V$, f = 100MHz (Fig.1)	—	2.5	3.5	dB

Note : I_{DSS} Classification O : 1.0~3.0, Y : 2.5~6.0, GR : 5.0~10.0

Marking





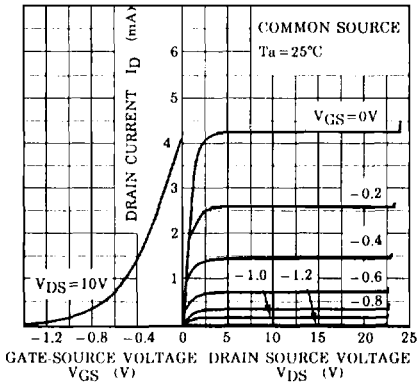
L_1 : 0.8mmϕ Ag PLATED Cu WIRE, 3. TURNS, 10mm ID, 10mm LENGTH.
L_2 : 0.8mmϕ Ag PLATED Cu WIRE, 3.5 TURNS, 10mm ID, 10mm LENGTH.

Fig.1 100MHz G_{PS}, NF TEST CIRCUIT

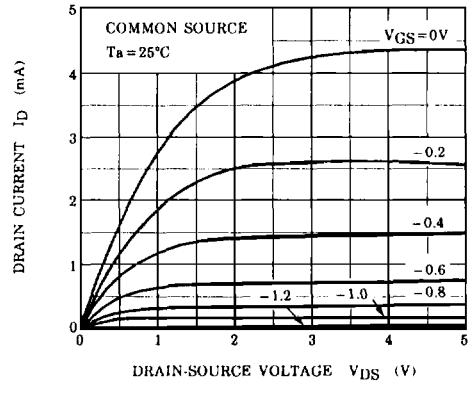
2SK881 is measured at each group by changing R_S.

GROUP	R_S (Ω)
2SK881-O	0
2SK881-Y	18Ω±5%
2SK881-GR	100Ω±5%

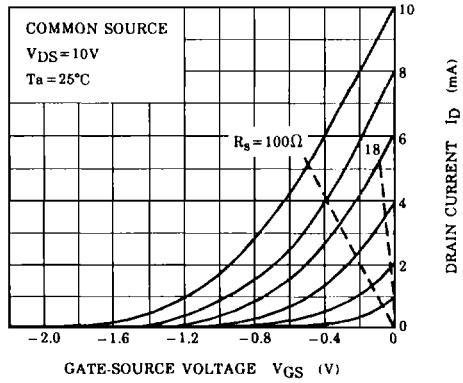
STATIC CHARACTERISTICS



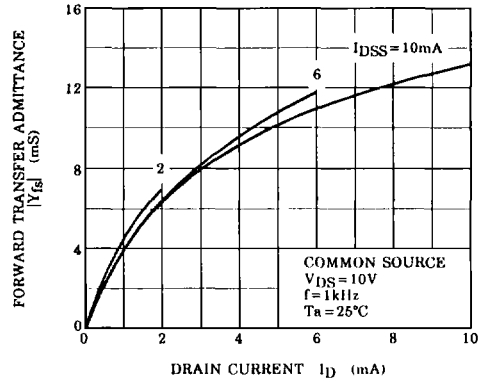
I_D – V_{DS} (LOW VOLTAGE REGION)



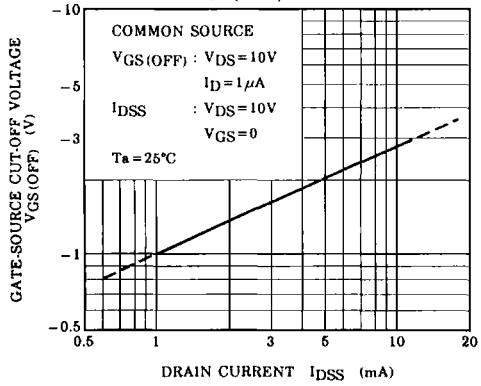
I_D – V_{GS}



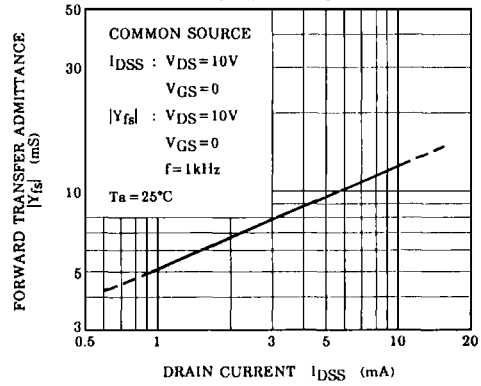
$|Y_{fs}|$ – I_D



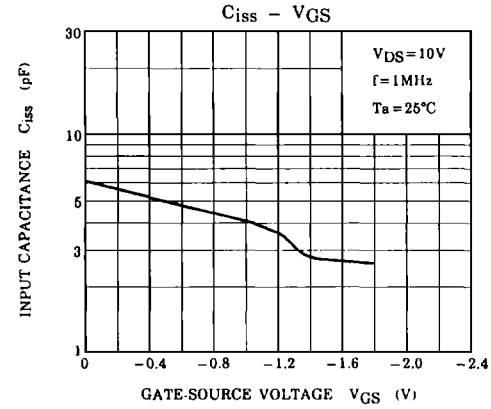
$V_{GS(OFF)}$ – I_{DSS}



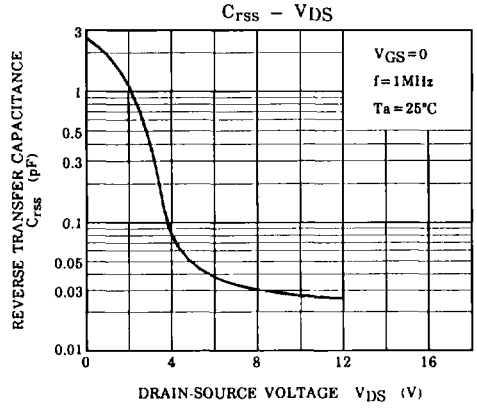
$|Y_{fs}|$ – I_{DSS}



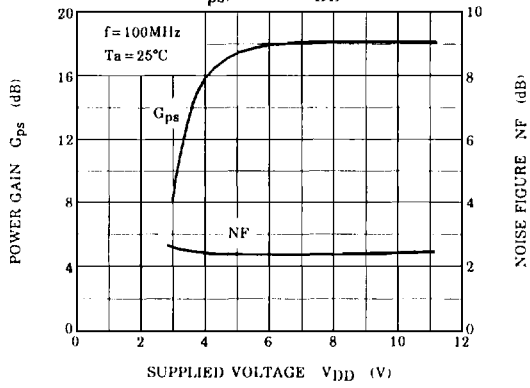
C_{iss} – V_{GS}



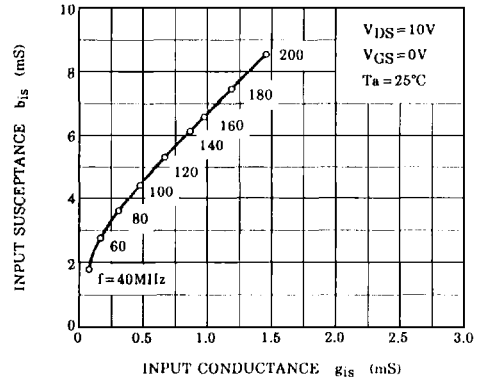
C_{rss} – V_{DS}



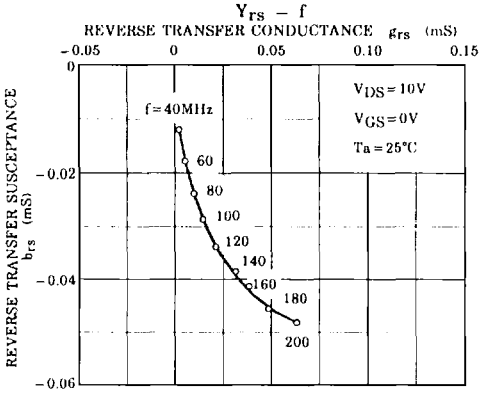
G_{ps}, NF – V_{DD}



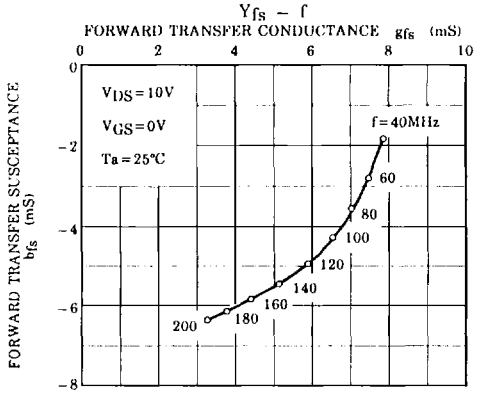
Y_{is} – f



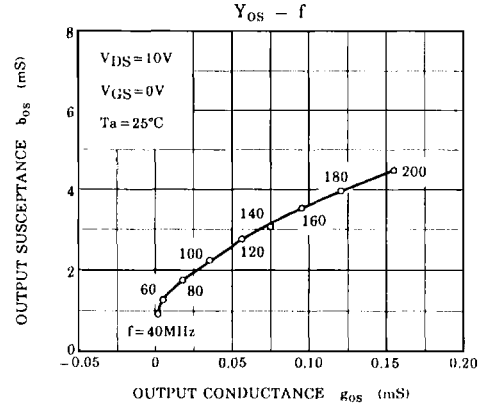
Y_{rs} – f



Y_{fs} – f



Y_{os} – f



P_D – Ta